



**TM014H03DF**

**N+N-Channel Enhancement Mosfet**

**General Description**

- Low  $R_{DS(ON)}$
- RoHS and Halogen-Free Compliant

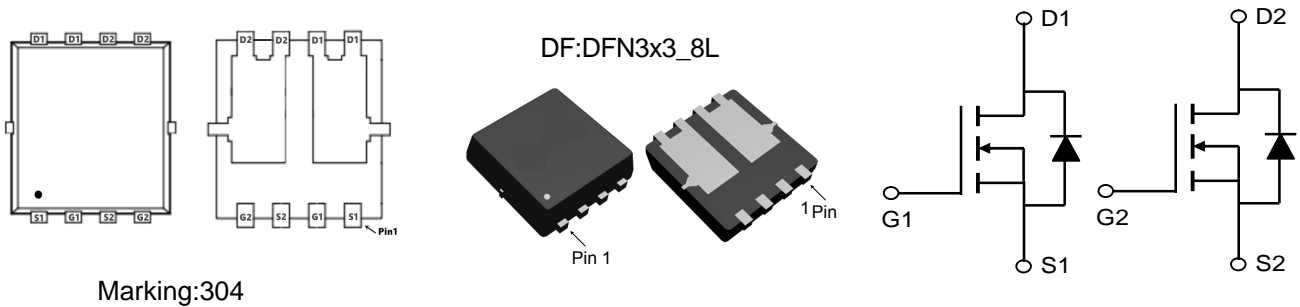
**Applications**

- Load switch
- PWM

**Product Summary**

$V_{DS} = 30V$   $I_D = 25A$   
 $R_{DS(ON)} = 14 m\Omega$  (Typ.) @  $V_{GS} = 10V$

100% UIS Tested  
 100%  $R_g$  Tested



**Absolute Maximum Ratings** ( $T_A = 25^\circ C$  Unless Otherwise Noted)

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	30	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	25	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	10	A
$I_{DM}$	Pulsed Drain Current <sup>2</sup>	56	A
EAS	Single Pulse Avalanche Energy <sup>3</sup>	12.1	mJ
$I_{AS}$	Avalanche Current	48	A
$P_D @ T_C = 25^\circ C$	Total Power Dissipation <sup>4</sup>	6.0	W
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ C$
$T_J$	Operating Junction Temperature Range	-55 to 150	$^\circ C$

**Thermal Data**

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient <sup>1</sup>	---	75	$^\circ C/W$

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**Electrical Characteristics** ( $T_J=25^{\circ}\text{C}$  unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
<b>Off Characteristic</b>						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	30	-	-	V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS}=30V, V_{GS}=0V$	-	-	1	$\mu A$
$I_{GSS}$	Gate to Body Leakage Current	$V_{DS}=0V, V_{GS}=\pm 20V$	-	-	$\pm 100$	nA
<b>On Characteristics</b>						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	1.0	1.5	2.5	V
$R_{DS(on)}$	Static Drain-Source on-Resistance <small>note2</small>	$V_{GS}=10V, I_D=5A$	-	14	20	m $\Omega$
		$V_{GS}=4.5V, I_D=3A$	-	18	29	m $\Omega$
<b>Dynamic Characteristics</b>						
$C_{iss}$	Input Capacitance	$V_{DS}=15V, V_{GS}=0V,$ $f=1.0MHz$	-	490	-	pF
$C_{oss}$	Output Capacitance		-	79	-	pF
$C_{rss}$	Reverse Transfer Capacitance		-	61	-	pF
$Q_g$	Total Gate Charge	$V_{DS}=15V, I_D=5.8A,$ $V_{GS}=10V$	-	5.2	-	nC
$Q_{gs}$	Gate-Source Charge		-	0.9	-	nC
$Q_{gd}$	Gate-Drain("Miller") Charge		-	1.3	-	nC
<b>Switching Characteristics</b>						
$t_{d(on)}$	Turn-on Delay Time	$V_{DS}=15V, I_D=3A,$ $V_{GS}=10V, R_{REN}=3\Omega$	-	4.5	-	ns
$t_r$	Turn-on Rise Time		-	2.5	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	14.5	-	ns
$t_f$	Turn-off Fall Time		-	3.5	-	ns
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
$I_S$	Maximum Continuous Drain to Source Diode Forward Current		-	-	12	A
$I_{SM}$	Maximum Pulsed Drain to Source Diode Forward Current		-	-	48	A
$V_{SD}$	Drain to Source Diode Forward Voltage	$V_{GS}=0V, I_S=12A$	-	-	1.2	V

**Diode Characteristics**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$I_S$	Continuous Source Current <sup>1,5</sup>	$V_G=V_D=0V$ , Force Current	---	---	25	A
$I_{SM}$	Pulsed Source Current <sup>2,5</sup>		---	---	56	A
$V_{SD}$	Diode Forward Voltage <sup>2</sup>	$V_{GS}=0V, I_S=1A, T_J=25^{\circ}\text{C}$	---	---	1.2	V

Note :

- The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper.
- The data tested by pulsed, pulse width  $\leq 300\mu s$ , duty cycle  $\leq 2\%$
- The EAS data shows Max. rating. The test condition is  $V_{DD}=25V, V_{GS}=10V, L=0.1mH, I_{AS}=21A$
- The power dissipation is limited by 150 $^{\circ}\text{C}$  junction temperature
- The data is theoretically the same as  $I_D$  and  $I_{DM}$ , in real applications, should be limited by total power dissipation.

### Typical Performance Characteristics

Figure 1: Output Characteristics

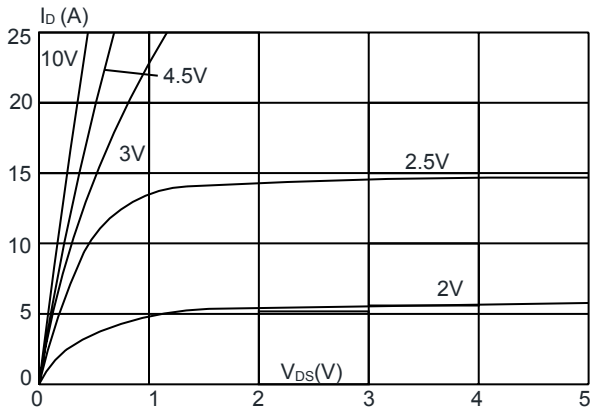


Figure 2: Typical Transfer Characteristics

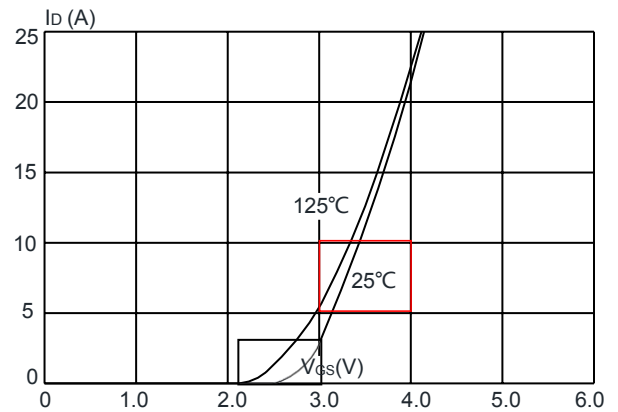


Figure 3: On-resistance vs. Drain Current

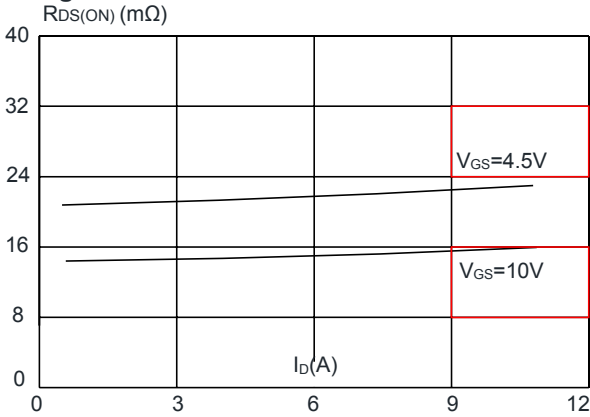


Figure 4: Body Diode Characteristics

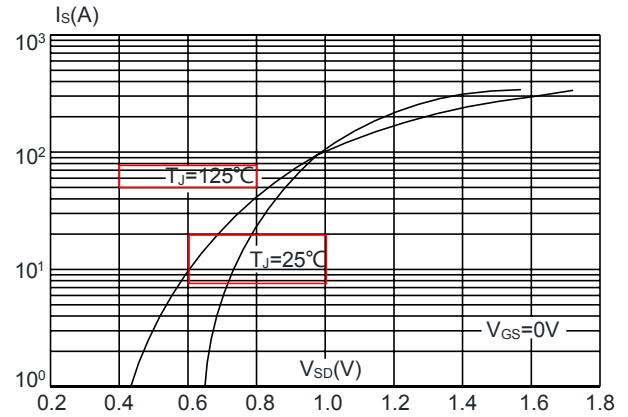


Figure 5: Gate Charge Characteristics

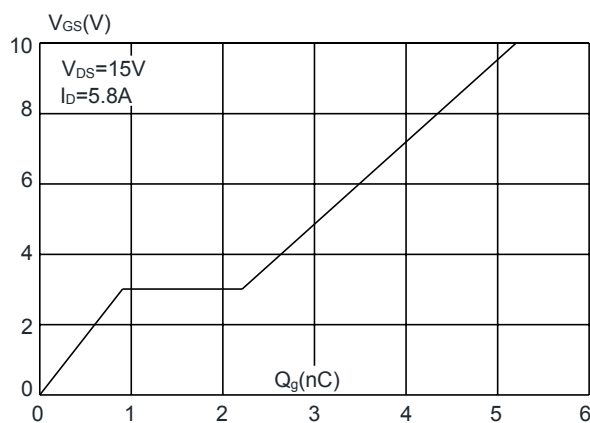
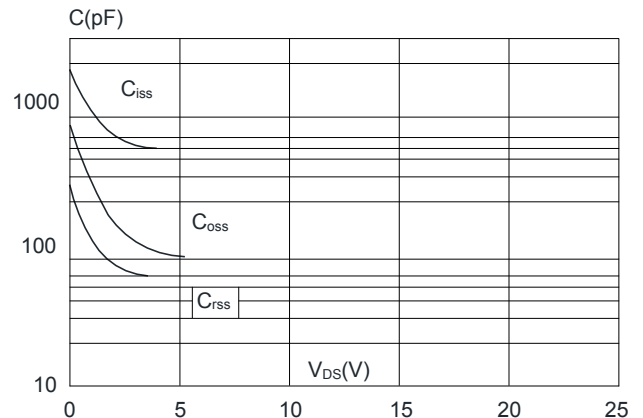


Figure 6: Capacitance Characteristics



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Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

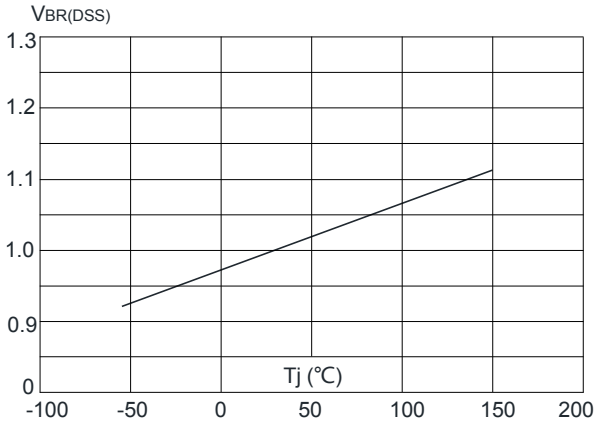


Figure 8: Normalized on Resistance vs. Junction Temperature

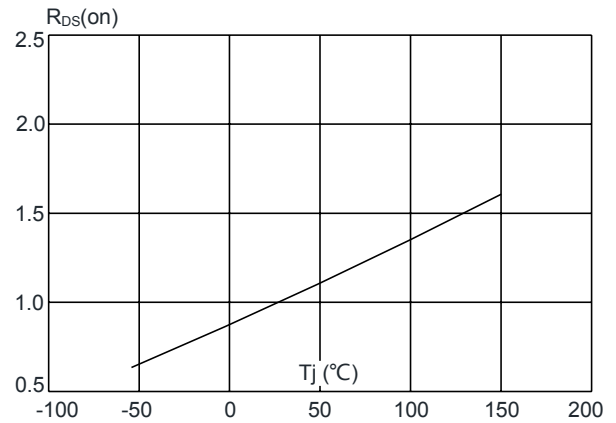


Figure 9: Maximum Safe Operating Area

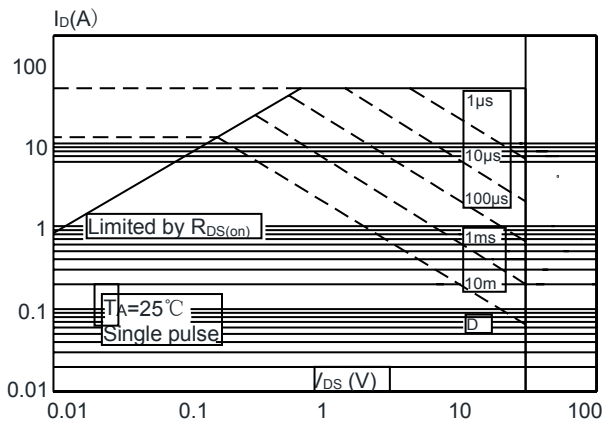


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

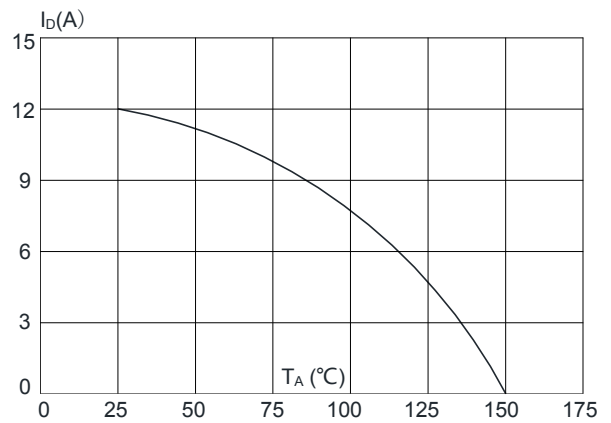
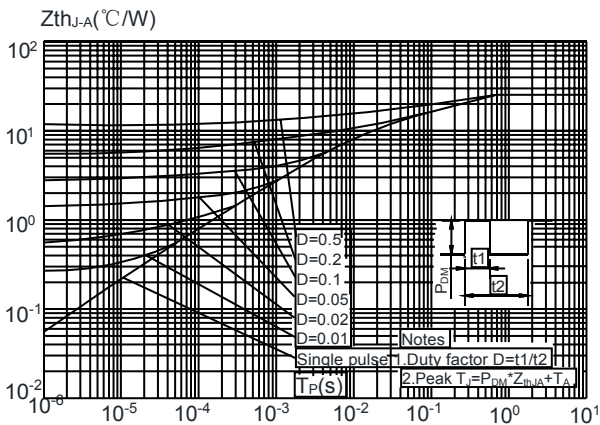
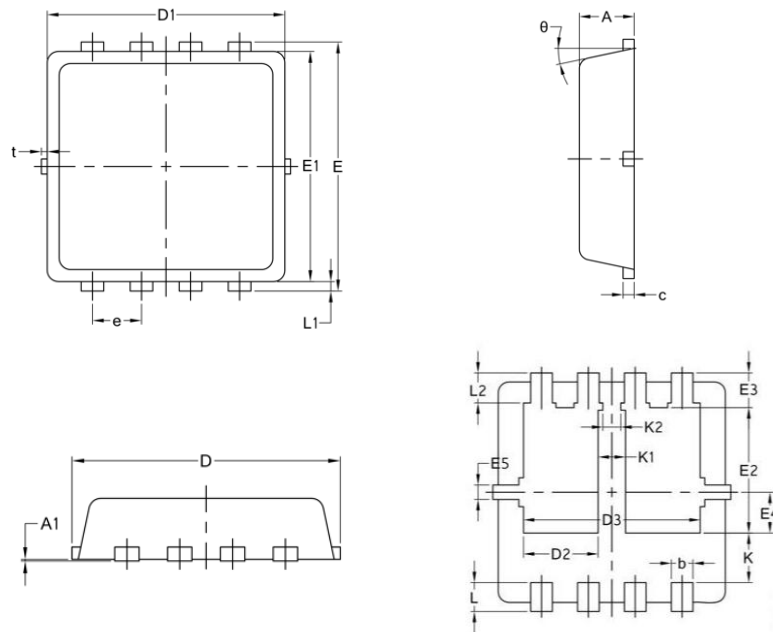


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient



## Package Mechanical Data:DFN3x3-8L



Symbol	Common		
	Mm		
	Min	Nom	Max
A	0.70	0.75	0.85
A1	/	/	0.05
b	0.25	0.30	0.39
c	0.14	0.152	0.20
D	3.20	3.30	3.45
D1	3.05	3.15	3.25
D2	0.84	1.04	1.24
D3	2.30	2.45	2.60
E	3.20	3.30	3.40
E1	2.95	3.05	3.15
E2	1.60	1.74	1.90
E3	0.28	0.48	0.65
E4	0.37	0.57	0.77
E5	0.10	0.20	0.30
e	0.60	0.65	0.70
K	0.50	0.69	0.80
K1	0.30	0.38	0.53
K2	0.15	0.25	0.35
L	0.30	0.40	0.50
L1	0.06	0.125	0.20
L2	0.27	0.42	0.57
t	0	0.075	0.13
Φ	10°	12°	14°

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